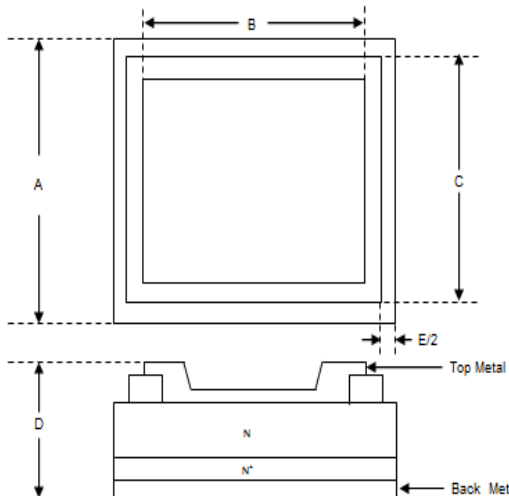


# BM82200BG

200V, 10A<sup>(1)</sup>, XTBR series Schottky

## Mechanical Data

Chip Drawing	Item	Information	
	Die Size (A)	2082 μm	82 mil
	Top Metal Pad Size (B)	1897 μm	74.7 mil
	Passivation Seal (C)	2002 μm	78.8 mil
	Wafer Thickness (D)	254±15 μm	10±0.6 mil
	Scribe Line Width (E)	80μm	3.15 mil
	Wafer Diameter	6 inch	
	Gross Die	3584	
	Top Side Metallization/ Layer Thickness	Ag / 3 ±0.3 μm	
	Back Side Metallization/ Layer Thickness	Ag / 2 ±0.2 μm	
	Recommended Storage Environment	Store in original container, in dry nitrogen, (6 months at an ambient temperature of 23°C±3°C)	

## Electrical Characteristics in C/P test (T<sub>J</sub>=25°C)

Parameter	Description	Min.	Typ.	Max.	Unit	Test Condition
V <sub>BR</sub>	Reverse Breakdown Voltage	200	—	—	V	I <sub>R</sub> =300μA
V <sub>F</sub>	Instantaneous Forward Voltage	—	0.74	0.78	V	I <sub>F</sub> =3A <sup>(2)</sup>
		—	0.93	1.05	V	I <sub>F</sub> =10A <sup>(2)</sup>
I <sub>R</sub>	Reverse Leakage Current	—	5	10	μA	V <sub>R</sub> =200V
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature	-40°C to 150°C Max				